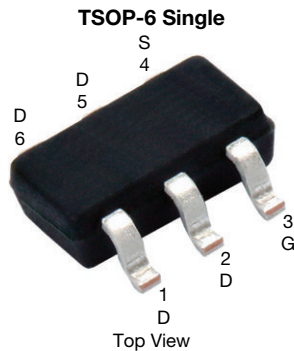


## P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A) <sup>a, e</sup>	Q <sub>g</sub> (TYP.)
-20	0.047 at V <sub>GS</sub> = -4.5 V	-4	9 nC
	0.080 at V <sub>GS</sub> = -2.7 V	-4	
	0.090 at V <sub>GS</sub> = -2.5 V	-4	



Marking Code: BN

**Ordering Information:**

Si3443DDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

**FEATURES**

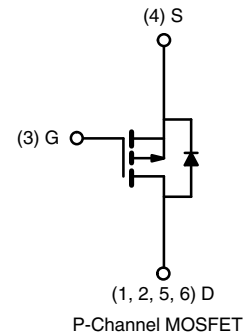
- TrenchFET® power MOSFET
- PWM optimized
- 100 % R<sub>g</sub> tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

**APPLICATIONS**

- Hard disk drives
- DC/DC converter
- Load switch
- Portable devices



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	± 12	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	-4 <sup>e</sup>	A
	T <sub>C</sub> = 70 °C	-4 <sup>e</sup>	
	T <sub>A</sub> = 25 °C	-4 <sup>b, c, e</sup>	
	T <sub>A</sub> = 70 °C	-3.9 <sup>b, c</sup>	
Pulsed Drain Current (t = 300 μs)	I <sub>DM</sub>	-20	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	-2.25	
	T <sub>A</sub> = 25 °C	-1.42 <sup>b, c</sup>	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	2.7	W
	T <sub>C</sub> = 70 °C	1.7	
	T <sub>A</sub> = 25 °C	1.7 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C	1.1 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 5 s	R <sub>thJA</sub>	61	74	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	38	46	

**Notes**

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 120 °C/W.
- Package limited.



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-20	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = -250 μA	-	-15	-	mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	2.8	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.6	-	-1.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	-	-	-1	μA
		V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	-10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ -5 V, V <sub>GS</sub> = -4.5 V	-20	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -4.7 A	-	0.039	0.047	Ω
		V <sub>GS</sub> = -2.7 V, I <sub>D</sub> = -1.4 A	-	0.057	0.080	
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -1.2 A	-	0.064	0.090	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -4.7 A	-	14	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	970	-	pF
Output Capacitance	C <sub>oss</sub>		-	125	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	111	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -8 V, I <sub>D</sub> = -4.9 A	-	20	30	nC
		V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -4.9 A	-	9	18	
Gate-Source Charge	Q <sub>gs</sub>		-	1.9	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.7	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	2.5	12.3	24.6	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -10 V, R <sub>L</sub> = 2.56 Ω I <sub>D</sub> ≅ -3.9 A, V <sub>GEN</sub> = -4.5 V, R <sub>g</sub> = 1 Ω	-	27	41	ns
Rise Time	t <sub>r</sub>		-	25	38	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	43	65	
Fall Time	t <sub>f</sub>		-	18	27	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	-2.25	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>		-	-	-20	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = -3.9 A	-	-0.85	-1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -3.9 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	11	20	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	3	6	nC
Reverse Recovery Fall Time	t <sub>a</sub>		-	6	-	ns
Reverse Recovery Rise Time	t <sub>b</sub>		-	5	-	

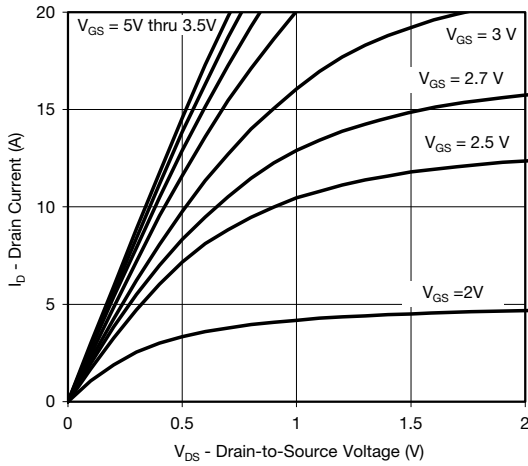
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

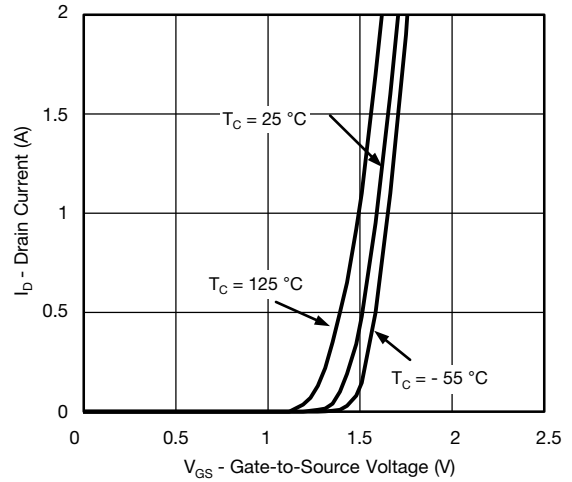
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



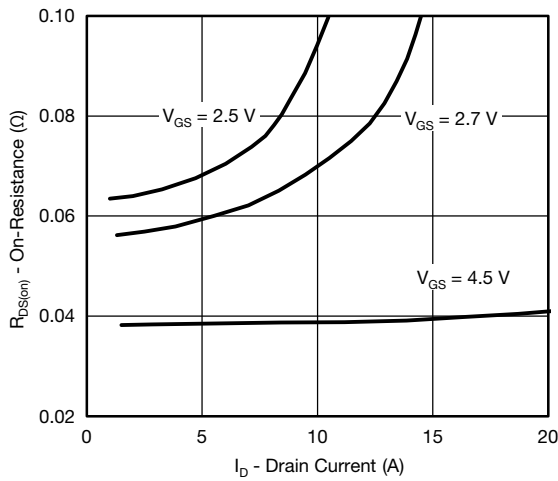
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



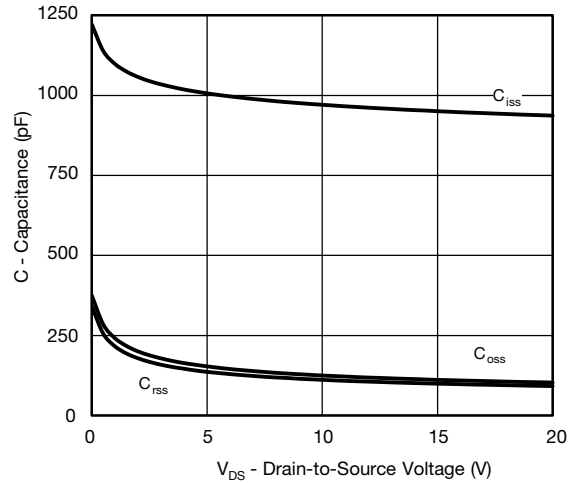
Output Characteristics



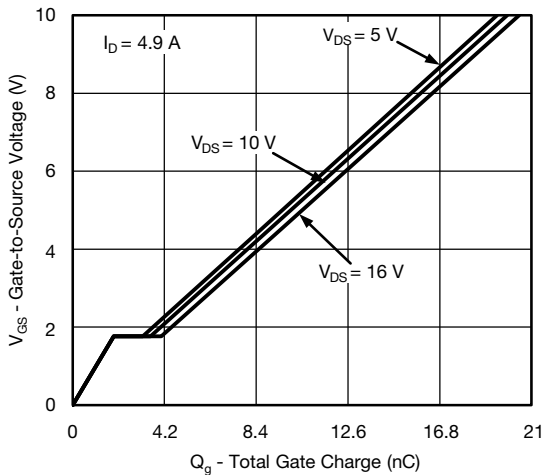
Transfer Characteristics



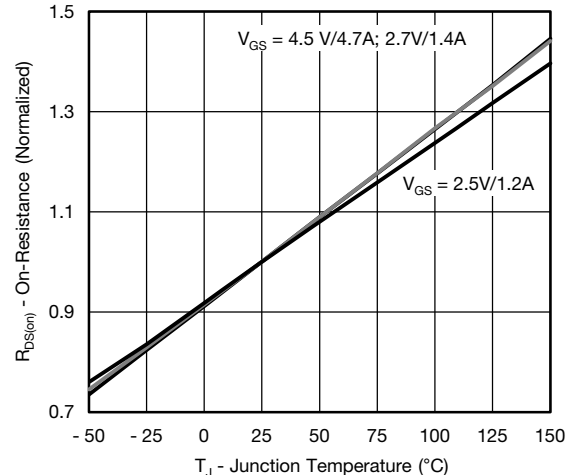
On-Resistance vs. Drain Current



Capacitance



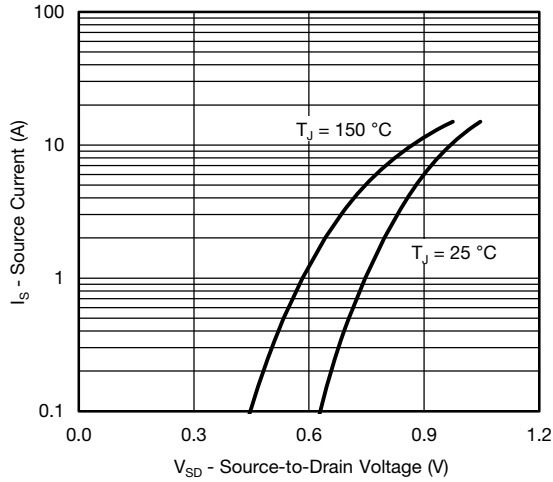
Gate Charge



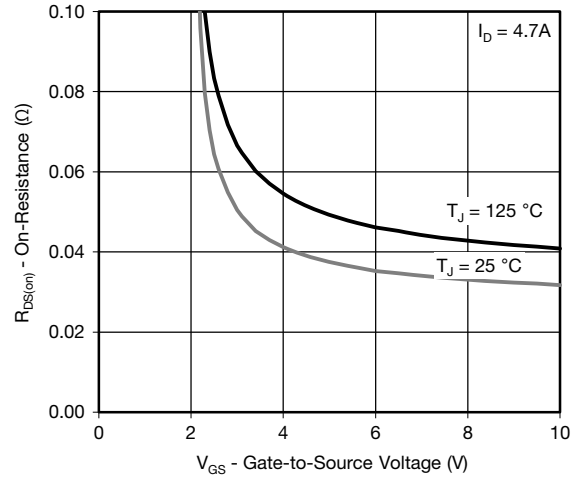
On-Resistance vs. Junction Temperature



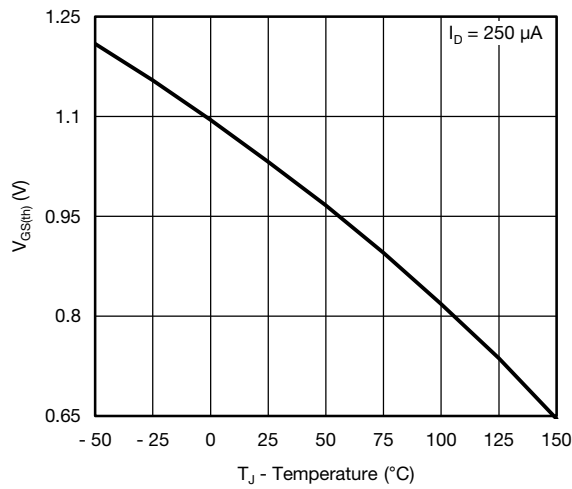
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



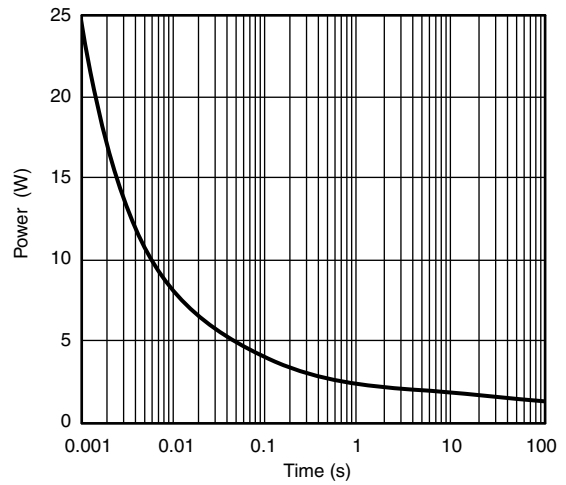
Source-Drain Diode Forward Voltage



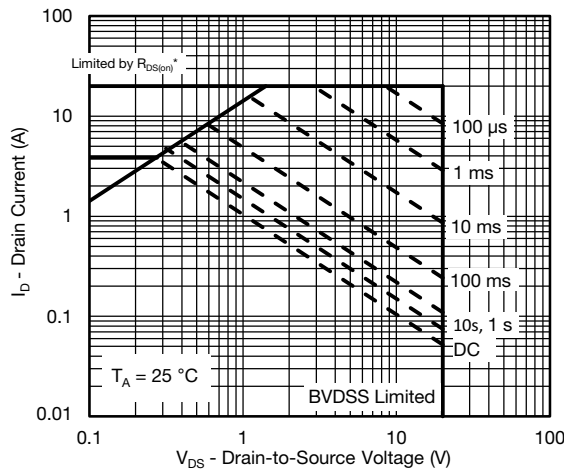
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



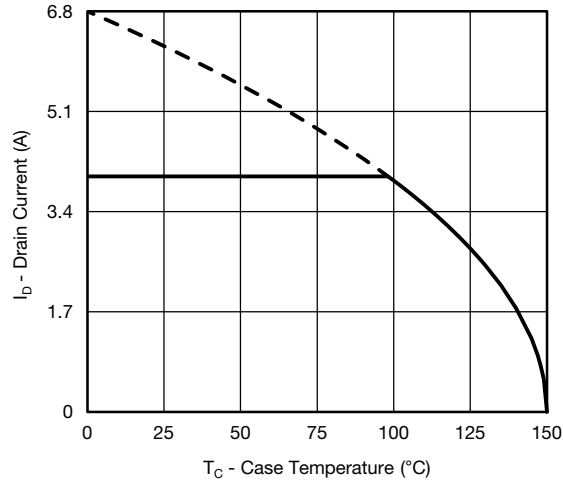
Single Pulse Power, Junction-to-Ambient



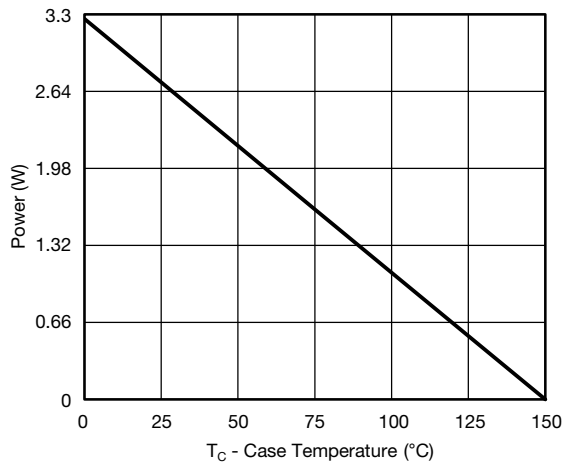
Safe Operating Area



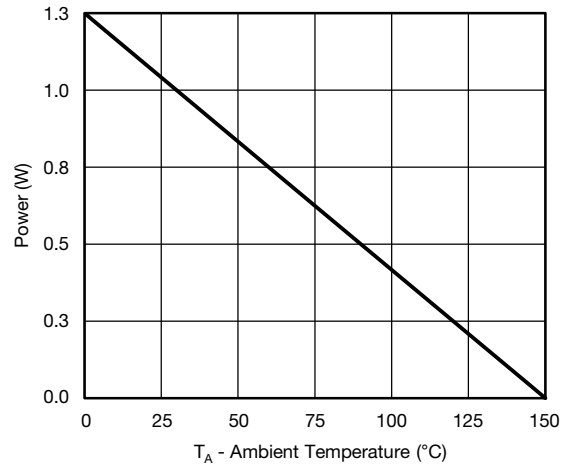
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating\***



**Power, Junction-to-Foot**

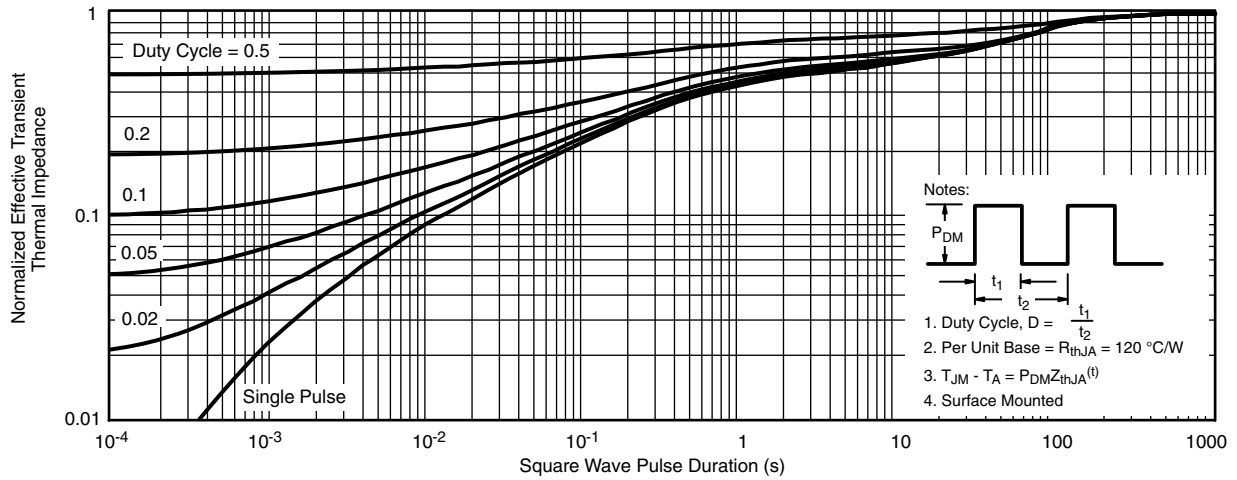


**Power, Junction-to-Ambient**

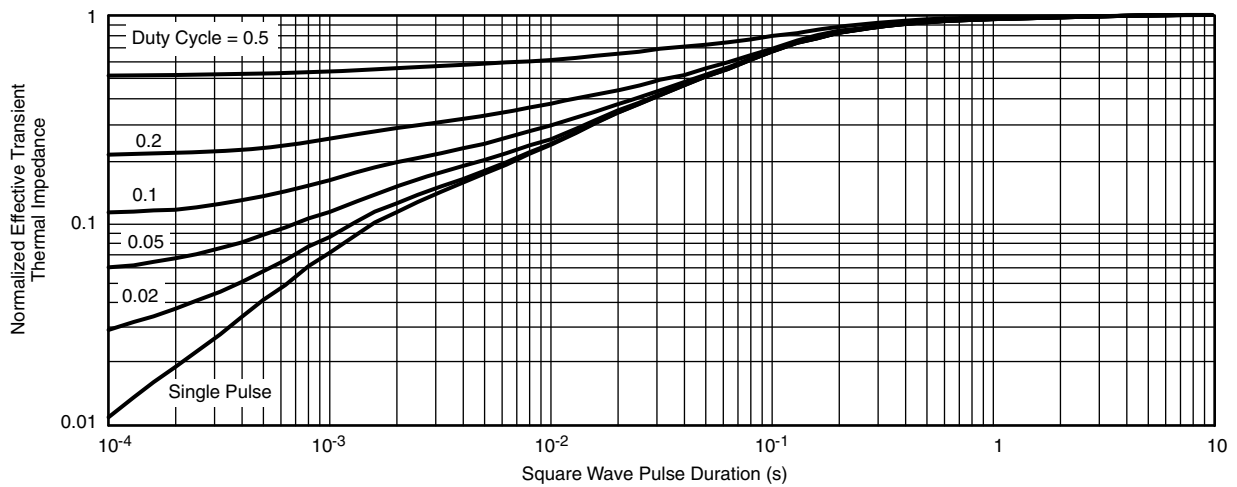
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C



5-LEAD TSOP



6-LEAD TSOP



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ <sub>1</sub>	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						



# Recommended Land Pattern For TSOP-5L / TSOP-6L



**Note**

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022  
 DWG: 3010





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